

Roll No.:

National Institute of Technology, Delhi

Name of the Examination: B. Tech (Make Up)

Branch : ECE

Semester : IV

Title of the Course : Analog Electronics

Course Code : ECB 252

Time: 3 Hours

Maximum Marks: 50

Note:

- Questions are printed on BOTH sides. Answers should be CLEAR AND TO THE POINT.
- All parts of a single question must be answered together. ELSE QUESTION SHALL NOT BE EVALUATED.

1. If a Si transistor used in the circuit (Figure 1) has minimum value of $\beta = h_{FE} = 30$ then determine whether the transistor is in cutoff, active or saturation region for $V_1 = 12V, V_2 = -12V, V_{CC} = 12V, R_1 = 15K, R_2 = 100K, R_L = 2.2K$. Also find output V_0 . [5]
2. Figure 2, shows the CB hybrid model. Find, h_{re} in terms of CB h parameter. [5]
3. Find the voltage gain (A_{vsf}) with feedback by taking source and load resistances in account of the circuit in figure 3. Also find R_{if} for the same circuit as well. Draw the small equivalent circuit model of the circuit given. [2+2]
[2]
4. Write short notes on following:
(a) Transistor switching times [2]
(b) Graphical analysis of transistor biasing [4]
(c) Collector- Emitter feedback bias circuit [3]
5. (a) What do you mean by feedback? [2]
(b) What are the advantages of negative feedback? [1]
(c) Define in details the four different classifications of basic amplifier. [4x2=8]
6. In the circuit shown in Fig. 4, $V_{CC} = 24V, R_C = 10 K\Omega$ and $R_E = 270 \Omega$. If a Si transistor is used with $\beta = 45$ and at quiescent condition, $V_{CE} = 5V$, determine (a) value of R (b) stability factor. [2+2]
7. Put "Tick (\checkmark)" Marks or Write T/ F on the write option wherever applicable (Bold). [10]
(a) A capacitor stores, **charge/energy/current**.
(b) The **blocking/coupling/bypass** capacitor prevents the flow of dc current from the collector circuit to load resistance.
(c) In a transistor, if the impedance between collector and emitter terminal is viewed as finite then the transistor is in **saturation/cutoff/ideal** region.
(d) Usually in a transistor, $R_b \approx 10R_c$ will drive into **weak saturation/hard cut off/hard saturation** region.
(e) Turn-on-time for a transistor = delay time + storage time. (T/F)
(f) Alloy is made up of compound semiconductors. (T/F).

- (g) White noise provides variation over BW. (T/F)
- (h) Stability factor of self-bias circuit is worst among other biasing circuits. (T/F)
- (i) Sensistor has negative temperature coefficient. (T/F)
- (j) Cascading and cascoding are same arrangement of transistor configurations. (T/F)
- =====

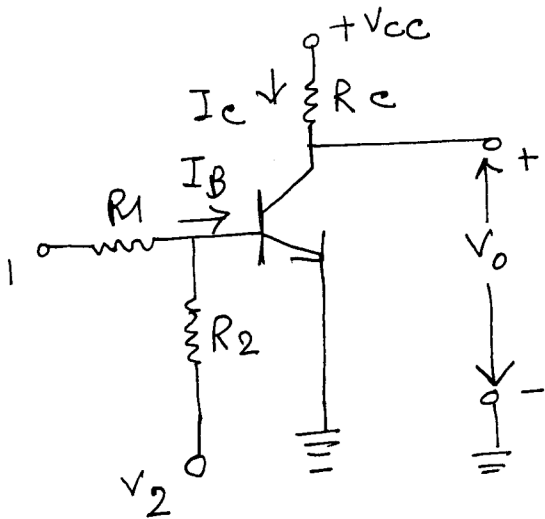


Figure 1.

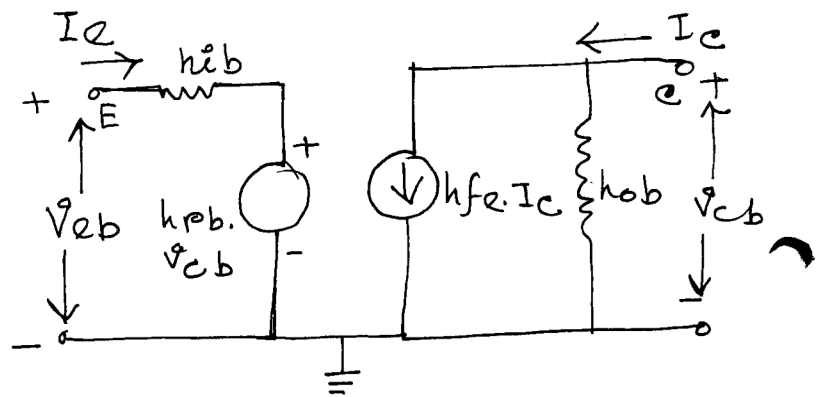


Figure 2

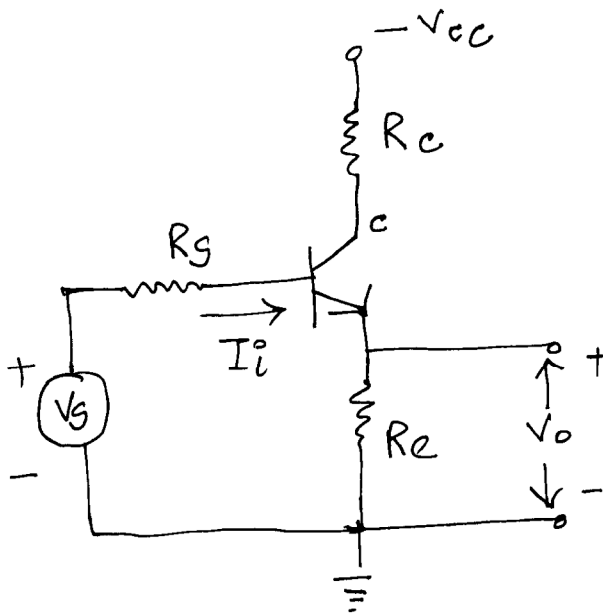


Figure 3

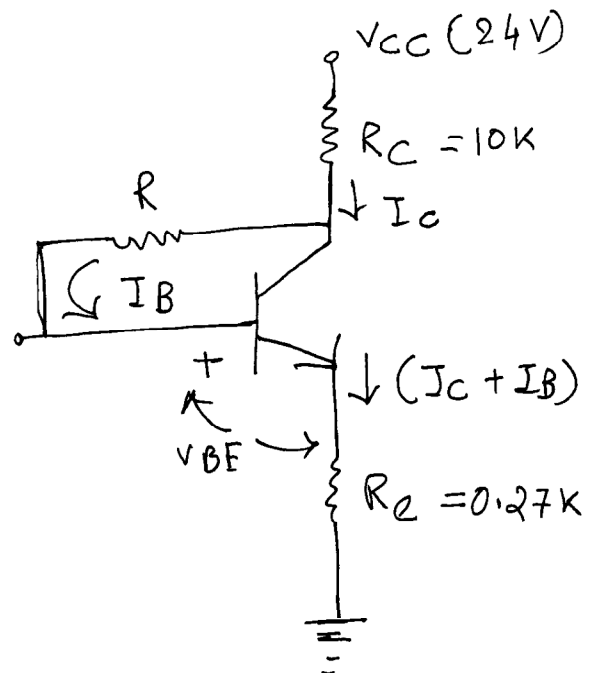


Figure 4